International IΘR Rectifier

IRF7311PbF

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Fully Avalanche Rated
- Lead-Free

S1 □□ 1   8 □□ D1
G1 □□ 2   7 □□ D1
S2 □□ 3   6 □□ D2
G2 □□ 4   5 □□ D2

Top View

$V_{DSS} = 20V$

$R_{DS(on)} = 0.029\Omega$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques.

SO-8
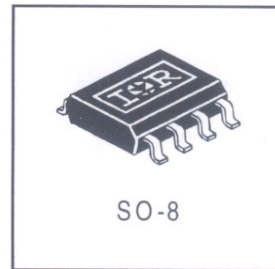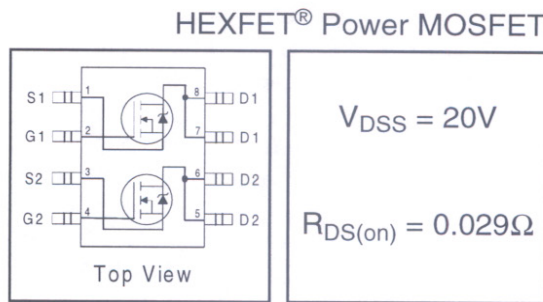
Absolute Maximum Ratings ($T_A = 25°C$ Unless Otherwise Noted)

		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current⑤	$T_A = 25°C$	I_D	6.6	A
	$T_A = 70°C$		5.3	
Pulsed Drain Current		I_{DM}	26	
Continuous Source Current (Diode Conduction)		I_S	2.5	
Maximum Power Dissipation ⑤	$T_A = 25°C$	P_D	2.0	W
	$T_A = 70°C$		1.3	
Single Pulse Avalanche Energy ②		E_{AS}	100	mJ
Avalanche Current		I_{AR}	4.1	A
Repetitive Avalanche Energy		E_{AR}	0.20	mJ
Peak Diode Recovery dv/dt ③		dv/dt	5.0	V/ ns
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to + 150	°C
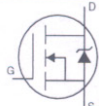
Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient⑤	$R_{\theta JA}$	62.5	°C/W

1

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.027	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.023	0.029	Ω	V_{GS} = 4.5V, I_D = 6.0A ④
		—	0.030	0.046		V_{GS} = 2.7V, I_D = 5.2A ④
$V_{GS(th)}$	Gate Threshold Voltage	0.7	—	—	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	—	20	—	S	V_{DS} = 10V, I_D = 6.0A
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V_{DS} = 16V, V_{GS} = 0V
		—	—	5.0		V_{DS} = 16V, V_{GS} = 0V, T_J = 55°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -12V
Q_g	Total Gate Charge	—	18	27	nC	I_D = 6.0A
Q_{gs}	Gate-to-Source Charge	—	2.2	3.3		V_{DS} = 10V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.2	9.3		V_{GS} = 4.5V, See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time	—	8.1	12	ns	V_{DD} = 10V
t_r	Rise Time	—	17	25		I_D = 1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	38	57		R_G = 6.0Ω
t_f	Fall Time	—	31	47		R_D = 10Ω ④
C_{iss}	Input Capacitance	—	900	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	430	—		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	—	200	—		f = 1.0MHz, See Fig. 9

Source-Drain Ratings and Characteristics

|	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	26		
V_{SD}	Diode Forward Voltage	—	0.72	1.0	V	T_J = 25°C, I_S = 1.7A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	52	77	ns	T_J = 25°C, I_F = 1.7A
Q_{rr}	Reverse Recovery Charge	—	58	86	nC	di/dt = 100A/μs ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 12mH
R_G = 25Ω, I_{AS} = 4.1A.

③ I_{SD} ≤ 4.1A, di/dt ≤ 92A/μs, V_{DD} ≤ $V_{(BR)DSS}$,
T_J ≤ 150°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ Surface mounted on 1 in square Cu board

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SO-8 Package Outline
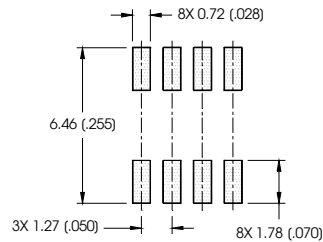
Dimensions are shown in milimeters (inches)
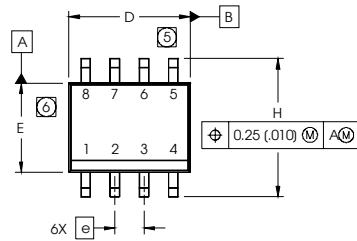
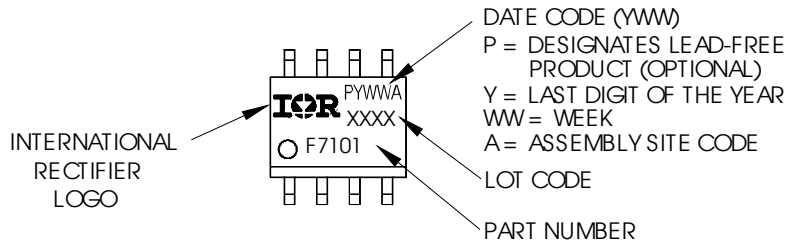| DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°
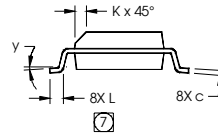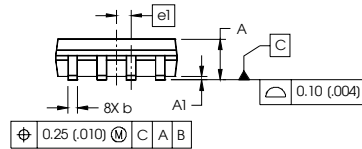
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
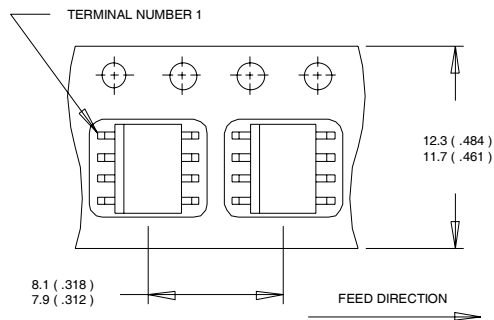7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT

8X 0.72 (.028)
6.46 (.255)
3X 1.27 (.050)
8X 1.78 (.070)

SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

DATE CODE (YWW)
P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)
Y = LAST DIGIT OF THE YEAR
WW = WEEK
A = ASSEMBLY SITE CODE

LOT CODE

PART NUMBER

INTERNATIONAL RECTIFIER LOGO

SO-8 Tape and Reel

Dimensions are shown in milimeters (inches)

TERMINAL NUMBER 1

12.3 (.484)
11.7 (.461)

8.1 (.318)
7.9 (.312)

FEED DIRECTION

NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.

$\varnothing$ 330.00
(12.992)
MAX.

14.40 (.566)
12.40 (.488)
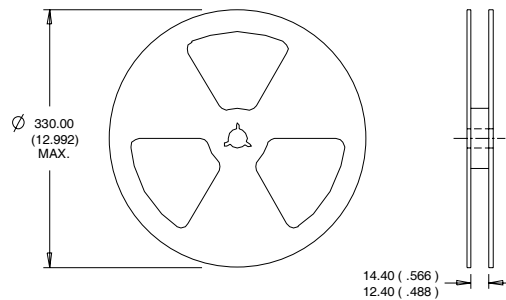
NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the consumer market.
Qualification Standards can be found on IR's Web site.

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